



Low-Voltage, Low r_{ON} , Dual SPST Analog Switch

FEATURES

- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance - $r_{DS(on)}$: 3.0 Ω
- Fast Switching - 12 ns
- Low Charge Injection - Q_{INJ} : 10 pC
- Low Power Consumption
- TTL/CMOS Compatible
- SOT23-8 and MSOP-8 Packages

BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits

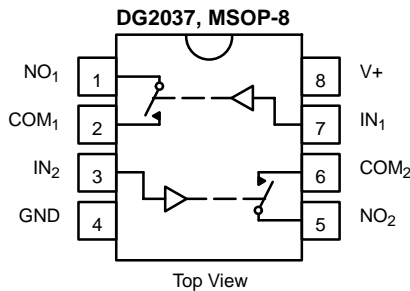
DESCRIPTION

The DG2037/2038/2039 are dual single-pole/single-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, fast switching, low on-resistance ($r_{DS(on)}$: 3.0 Ω @ 2.7 V) and small physical size, the DG2037/2038/2039 are ideal for portable and battery powered applications requiring high performance and efficient use of board space.

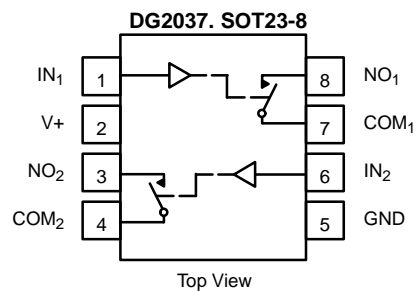
The DG2037/2038/2039 are built on Vishay Siliconix's new high density low voltage process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION—DG2037



Device Marking: 2037

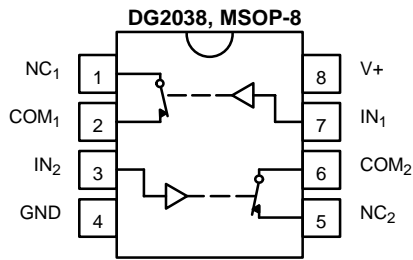


Device Marking: E0

TRUTH TABLE DG2037	
Logic	Switch
0	Off
1	On

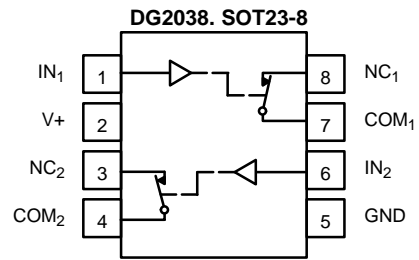


FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION—DG2038/DG2039



Top View

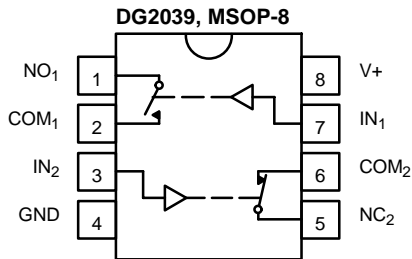
Device Marking: 2038



Top View

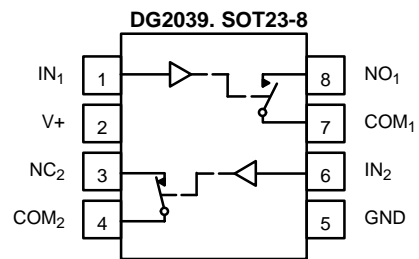
Device Marking: F1

TRUTH TABLE DG2038	
Logic	Switch
0	On
1	Off



Top View

Device Marking: 2039



Top View

Device Marking: F2

TRUTH TABLE DG2039		
Logic	Switch-1	Switch-2
0	Off	On
1	On	Off

ORDERING INFORMATION		
Temp Range	Package	Part Number
-40 to 85°C	MSOP-8	DG2037DQ
		DG2038DQ
		DG2039DQ
	SOT23-8	DG2037DS
		DG2038DS
		DG2039DS



ABSOLUTE MAXIMUM RATINGS

Reference to GND

V+ -0.3 to 6.0 V

IN, COM, NC, NO^a -0.3 V to (V+ + 0.3 V)

Continuous Current (Any terminal) ±50 mA

Peak Current ±200 mA
(Pulsed at 1 ms, 10% duty cycle)

Storage Temperature (D Suffix) -65 to 150°C

Power Dissipation (Packages)^b

MSOP-8^c 320 mW

SOT23-8^c 515 mW

- Notes:
- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
 - b. All leads welded or soldered to PC Board.
 - c. Derate 6.5 mW/°C above 25°C

SPECIFICATIONS (V+ = 3.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3 V, ±10%, V _{IN} = 0.4 or 1.5 V ^e	Temp ^a	Limits -40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room Full		3	6 7	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 2.7 V, V _{COM} = 1.5 to V+, I _{NO} , I _{NC} = 10 mA	Room		0.5		
r _{ON} Match ^d	r _{ON} Match	V+ = 2.7 V, V _D = 1.5 to V+, I _D = 10 mA	Room		0.3		
Switch Off Leakage Current	I _{NO(off)} , I _{NC(off)}	V+ = 3.3 V V _{NO} , V _{NC} = 1 V/3 V, V _{COM} = 3 V/1 V	Room Full	-1 -10		1 10	nA
	I _{COM(off)}		Room Full	-1 -10		1 10	
Channel-On Leakage Current	I _{COM(on)}	V+ = 3.3 V, V _{NO} , V _{NC} = V _{COM} = 1 V/3 V	Room Full	-1 -10		1 10	
Digital Control							
Input High Voltage	V _{INH}		Full	1.5			V
Input Low Voltage	V _{INL}		Full			0.4	
Input Capacitance ^d	C _{in}	f = 1 MHz	Full		8		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	-1		1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	V _{NO} or V _{NC} = 2.0 V, R _L = 300 Ω, C _L = 35 pF Figure 1 and 2	Room Full		22	35 40	ns
Turn-Off Time	t _{OFF}		Room Full		17	31 35	
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω, Figure 3	Room		1		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		-61		dB
Crosstalk ^d	X _{TALK}		Room		-67		
Source-Off Capacitance ^d	C _{NC/NO(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		17		pF
Drain-Off Capacitance ^d	C _{COM(off)}		Room		19		
Channel-On Capacitance ^d	C _{ON}		Room		35		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	I+	V _{IN} = 0 or V+			0.02	1.0	μA
Power Consumption	P _C						3.3



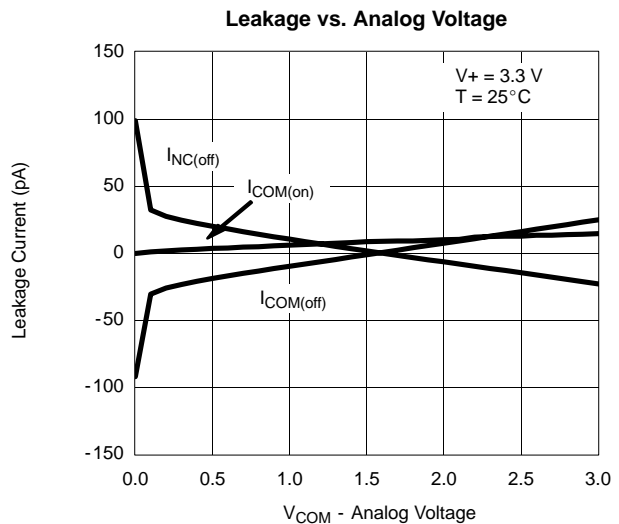
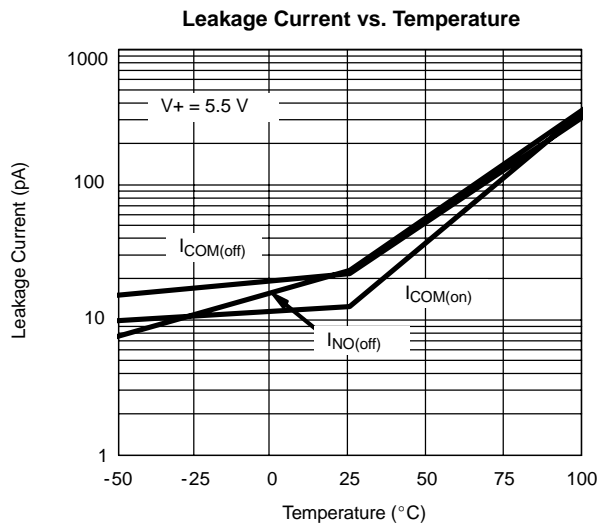
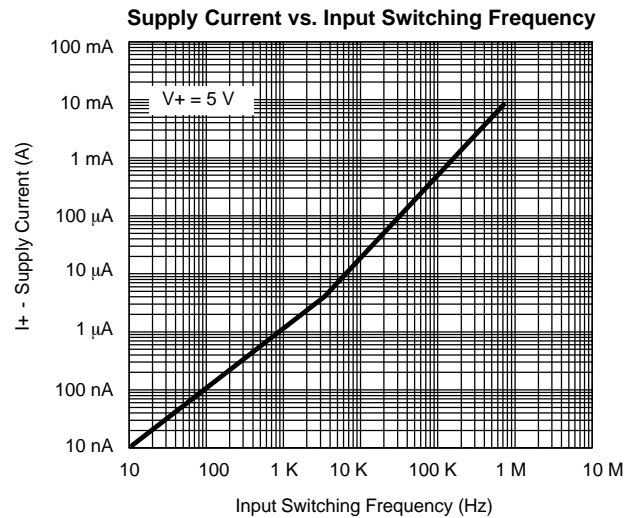
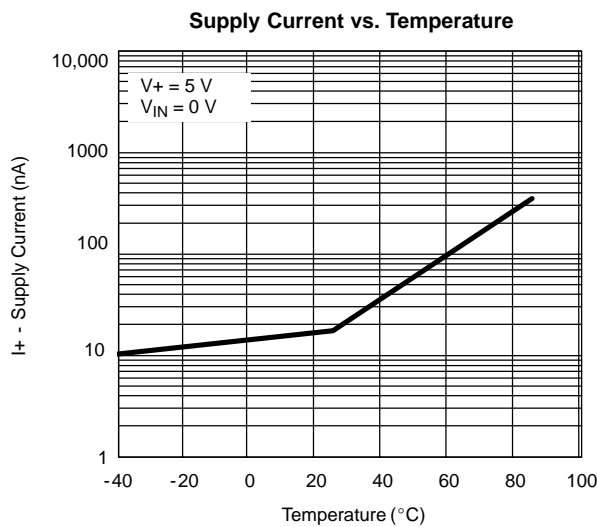
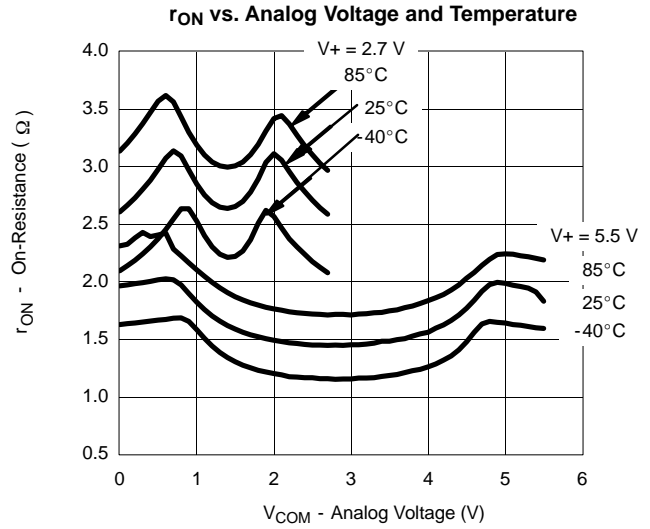
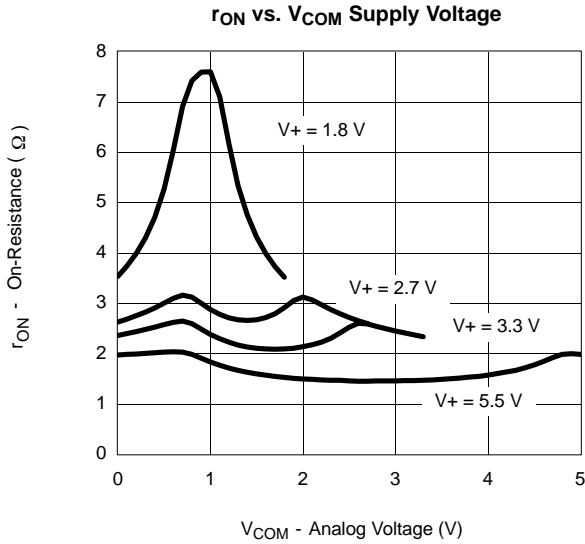
SPECIFICATIONS (V+ = 5.0 V)							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5 V, ± 10%, VIN = 0.8 or 2.4 V ^e	Temp ^a	Limits -40 to 85°C			Unit
				Min ^b	Typ ^c	Max ^b	
Analog Switch							
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 4.5 V, V _{COM} = 2.5 V, I _{NO} , I _{NC} = 10 mA	Room Full		2.5 1.6	5 6	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	V+ = 4.5 V, V _{COM} = 2.5 to V+, I _{NO} , I _{NC} = 10 mA	Room		0.4		
r _{ON} Match ^d	r _{ON} Match	V+ = 4.5 V, I _D = 10 mA, V _{COM} = 2.5 V	Room		0.2		
Switch Off Leakage Current ^f	I _{NO(off)} , I _{NC(off)}	V+ = 5.5 V V _{NO} , V _{NC} = 1 V/4.5 V, V _{COM} = 4.5 V/1 V	Room Full	-1 -10		1 10	nA
	I _{COM(off)}		Room Full	-1 10		1 10	
Channel-On Leakage Current ^f	I _{COM(on)}	V+ = 5.5 V V _{NO} , V _{NC} = V _{COM} = 1 V/4.5 V	Room Full	-1 -10		1 10	
Digital Control							
Input High Voltage	V _{INH}		Full	2.4			V
Input Low Voltage	V _{INL}		Full			0.8	
Input Capacitance	C _{in}	f = 1 MHz	Full		8		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	-1		1	μA
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V _{NO} or V _{NC} = 3 V, R _L = 300 Ω, C _L = 35 pF Figure 1 and 2	Room Full		19	30 35	ns
Turn-Off Time ^d	t _{OFF}		Room Full		12	22 30	
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R _{GEN} = 0 Ω, Figure 3	Room		1		pC
Off-Isolation ^d	OIRR	R _L = 50 Ω, C _L = 5 pF, f = 1 MHz	Room		-61		dB
Crosstalk ^d	X _{TALK}		Room		-67		
Source-Off Capacitance ^d	C _{NC/NO(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		15		pF
Drain-Off Capacitance ^d	C _{COM(off)}		Room		17		
Channel-On Capacitance ^d	C _{ON}		Room		35		
Power Supply							
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	I+	V _{IN} = 0 or V+			0.02	1.0	μA
Power Consumption	P _C						5.5

Notes:

- Room = 25°C, Full = as determined by the operating suffix.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Typical values are for design aid only, not guaranteed nor subject to production testing.
- Guarantee by design, nor subjected to production test.
- V_{IN} = input voltage to perform proper function.
- Not production tested.



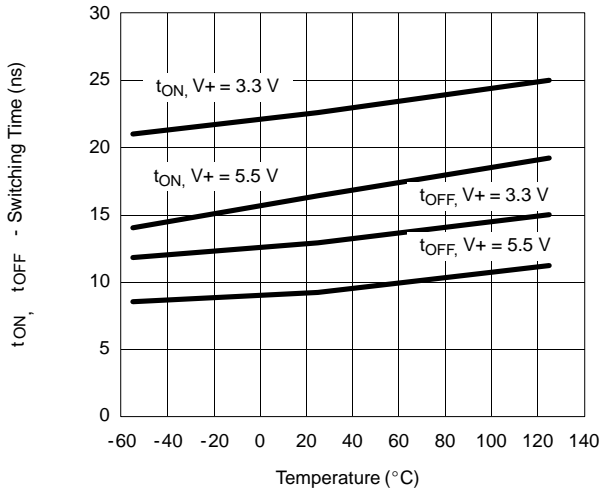
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



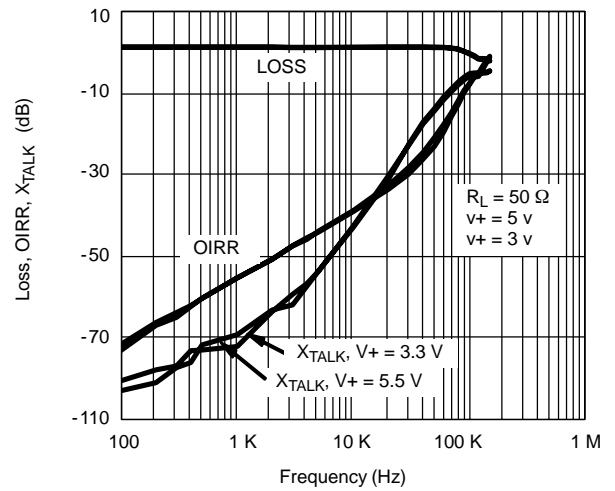


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

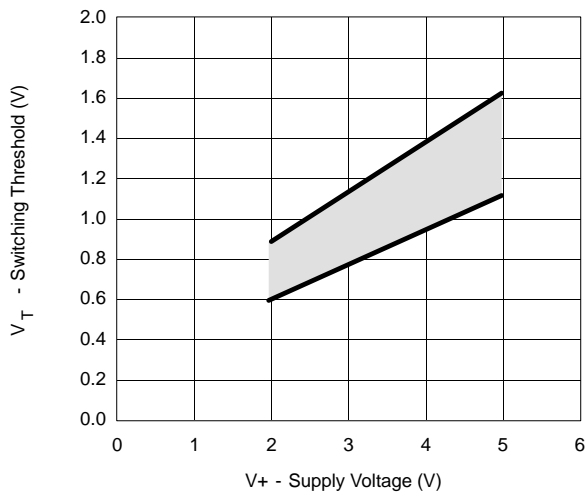
Switching Time vs. Temperature and Supply Voltage



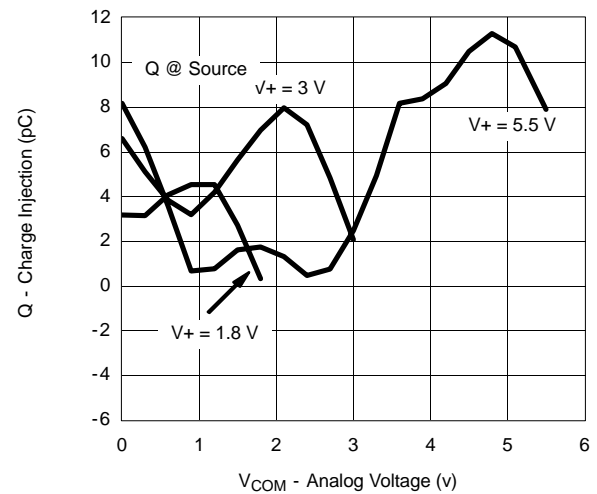
Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

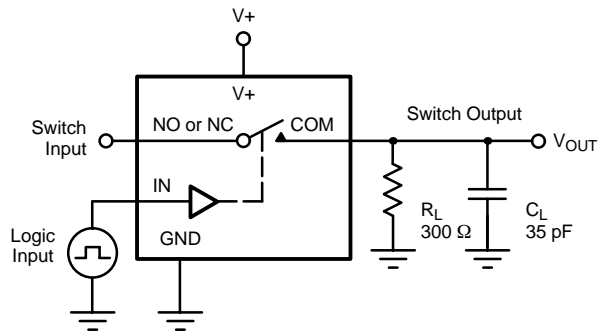


Switching Threshold vs. Supply Voltage



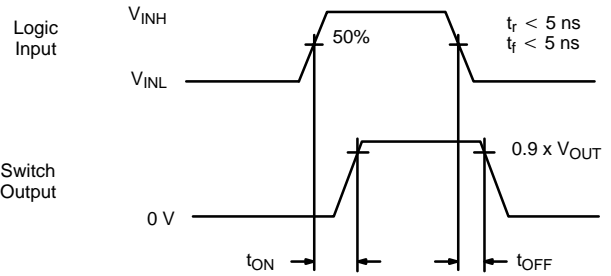
Charge Injection vs. Analog Voltage



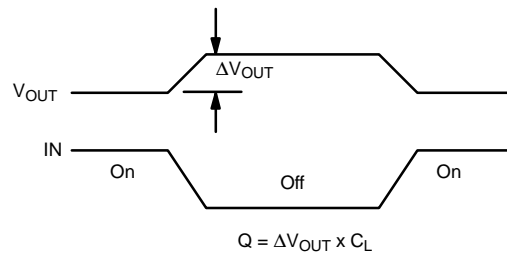
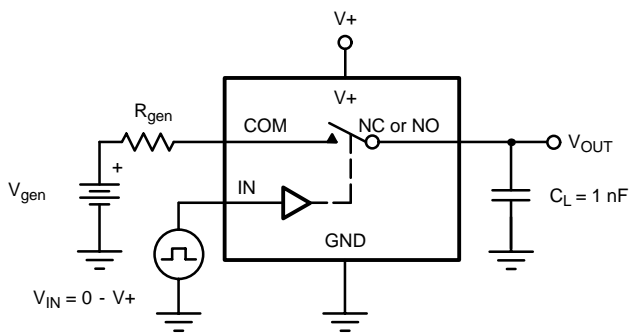
TEST CIRCUITS


C_L (includes fixture and stray capacitance)

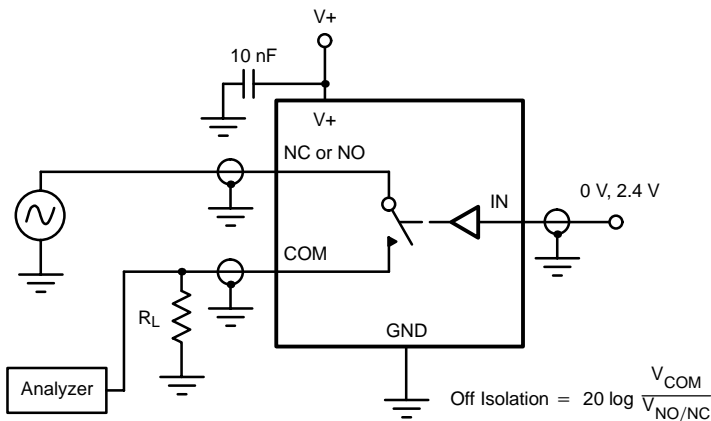
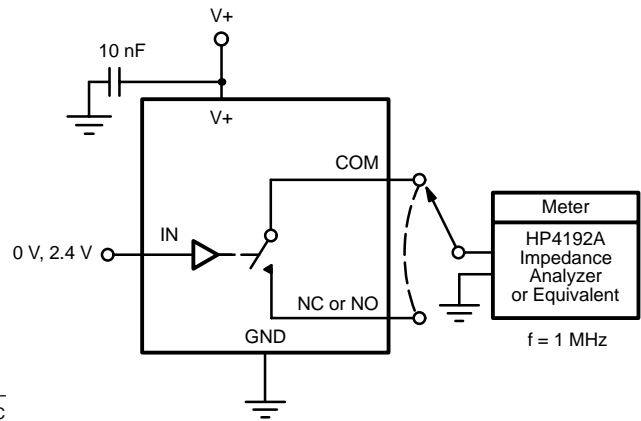
$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On
 Logic input waveforms inverted for switches that have the opposite logic sense.

FIGURE 1. Switching Time


IN depends on switch configuration: input polarity determined by sense of switch.

FIGURE 2. Charge Injection

FIGURE 3. Off-Isolation

FIGURE 4. Channel Off/On Capacitance